Product data sheet

1. General description

PNP low V_{CEsat} transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS302NX

2. Features and benefits

- · Low collector-emitter saturation voltage VCEsat
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- · High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

3. Applications

- DC-to-DC conversion
- MOSFET gate driving
- Motor control
- Charging circuits
- · Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-20	٧
I _C	collector current		-	-	-5.1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-10.2	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -4 A; I_B = -200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	32	48	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		, , , , , , , , , , , , , , , , , , ,
3	В	base	3 2 1	B—[
			SOT89	sym132

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS302PX		plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS302PX	%5J

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

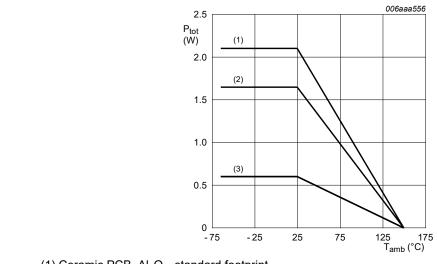
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-20	V
V_{CEO}	collector-emitter voltage	open base		-	-20	V
V_{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-5.1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-10.2	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.6	W
			[2]	-	1.65	W
			[3]	-	2.1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- 1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

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- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

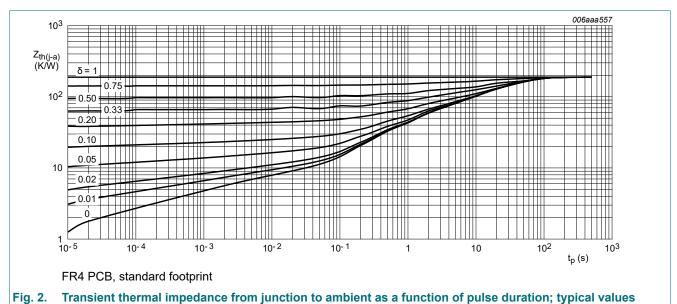
Power derating curves Fig. 1.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	208	K/W
junction to ambient		[2]	-	-	76	K/W	
]	[3]	-	-	60	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	20	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



Product data sheet

20 V, 5.1 A PNP low VCEsat transistor

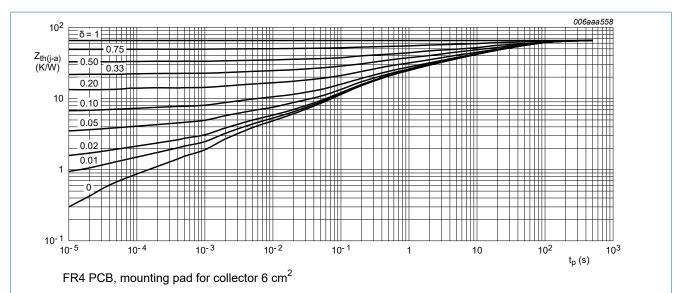


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

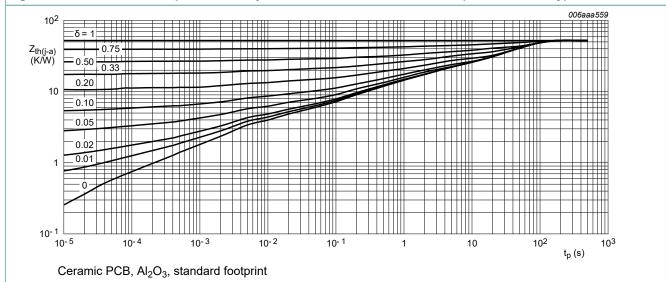


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Ісво	collector-base cut-off	V _{CB} = -20 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -20 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
Ево	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	250	370	-	
		V_{CE} = -2 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	250	340	-	
		V_{CE} = -2 V; I_{C} = -2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	290	-	
		V_{CE} = -2 V; I_{C} = -4 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	150	220	-	
		V_{CE} = -2 V; I_{C} = -6 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	160	-	
OLOGI	collector-emitter saturation voltage	I_C = -0.5 A; I_B = -50 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-25	-35	mV
		I_C = -1 A; I_B = -50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-45	-65	mV
		I_C = -1 A; I_B = -10 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-70	-100	mV
		I_C = -2 A; I_B = -40 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-90	-130	mV
		I_C = -4 A; I_B = -200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-130	-190	mV
		I_C = -4 A; I_B = -400 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-120	-175	mV
		I_C = -4 A; I_B = -40 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-200	-300	mV
		I_C = -5.1 A; I_B = -255 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-160	-230	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = -4 A; I_B = -200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	32	48	mΩ
		I_C = -4 A; I_B = -40 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	50	75	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = -1 A; I_B = -100 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.82	-0.9	V
		I_C = -4 A; I_B = -400 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.93	-1.05	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I_{C} = -2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.76	-0.85	V
d	delay time	$V_{CC} = -12.5 \text{ V}; I_C = -3 \text{ A}; I_{Bon} = -0.15 \text{ A};$	-	10	-	ns
r	rise time	I _{Boff} = 0.15 A; T _{amb} = 25 °C	-	55	-	ns
ton	turn-on time	$00 \text{ μs}; \delta \le 0.02; T_{amb} = 25 \text{ °C}$ $00 \text{ μs}; \delta \le 0.02; T_{amb} = 25 \text{ °C}$ $00 \text{ μs}; \delta \le 0.02; T_{amb} = 25 \text{ °C}$	-	65	=	ns
L _s	storage time		-	205	-	ns
t _f	fall time		-	145	-	ns
t _{off}	turn-off time		-	350	-	ns

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -0.1 A; f = 100 MHz; T_{amb} = 25 °C	-	130	-	MHz
C _c	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	130	160	pF

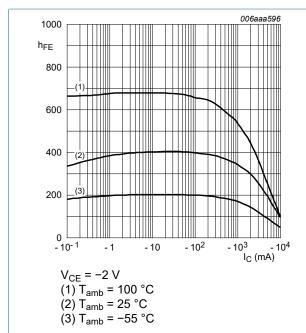


Fig. 5. DC current gain as a function of collector current; typical values

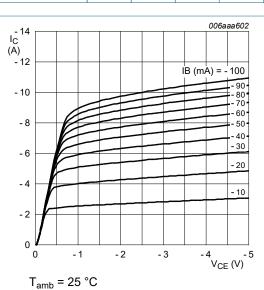


Fig. 6. Collector current as a function of collectoremitter voltage; typical values

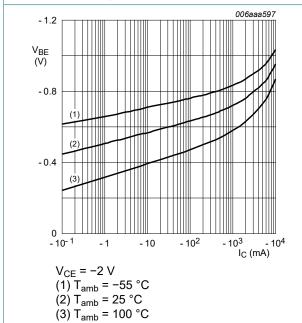
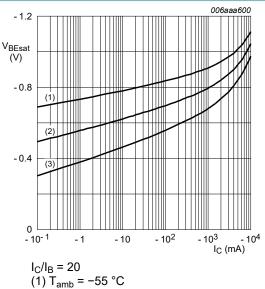


Fig. 7. Base-emitter voltage as a function of collector current; typical values



 $I_{C}/I_{B} = 20$ (1) $T_{amb} = -55 \,^{\circ}\text{C}$ (2) $T_{amb} = 25 \,^{\circ}\text{C}$ (3) $T_{amb} = 100 \,^{\circ}\text{C}$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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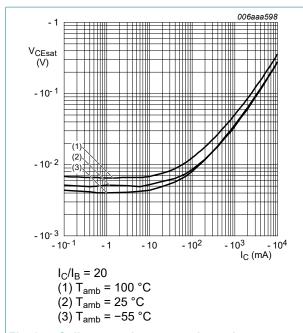


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

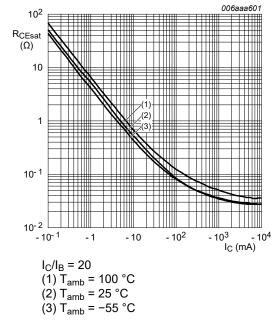


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

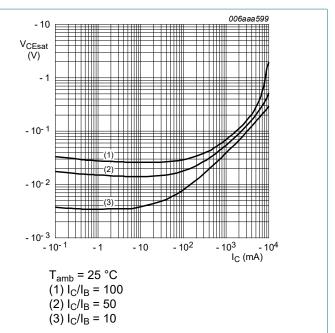


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

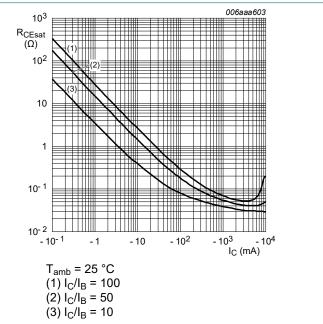
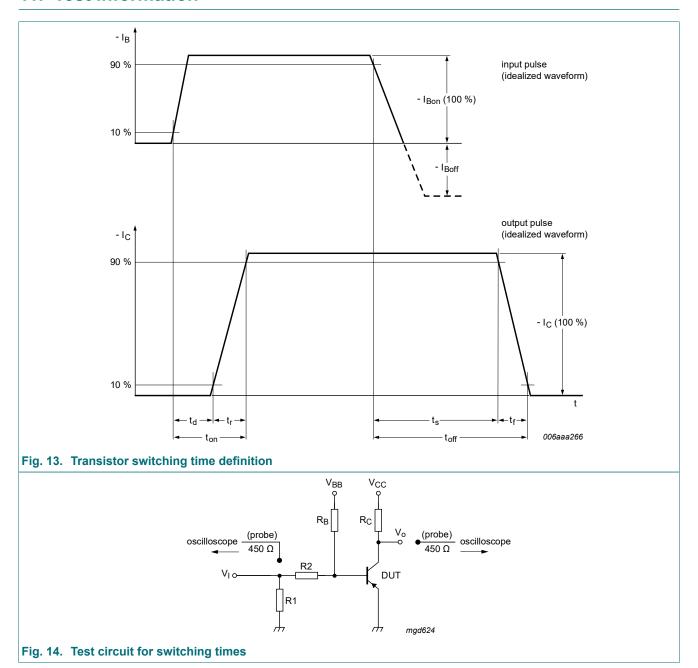


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

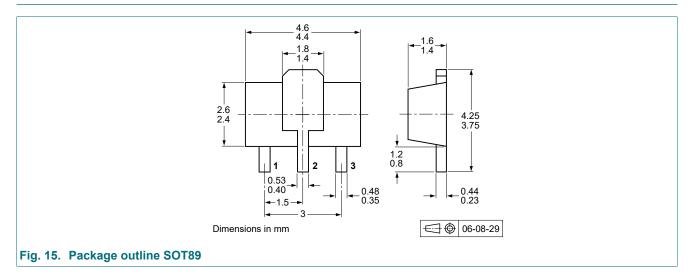


Quality information

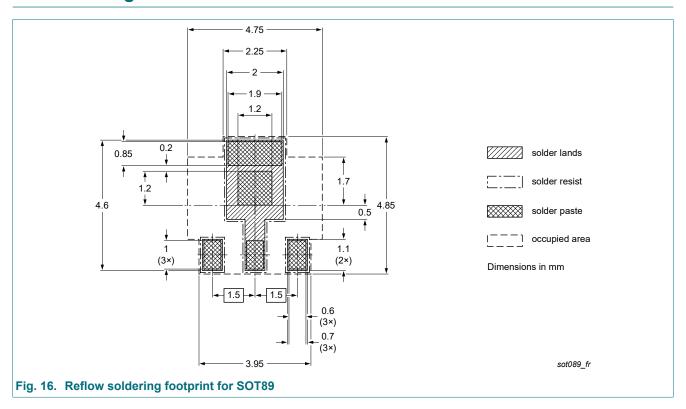
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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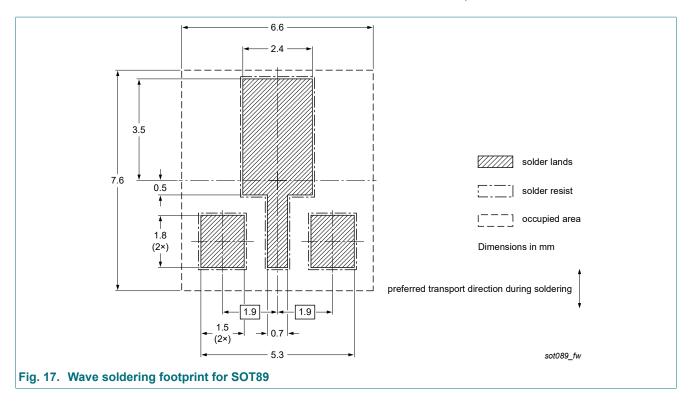
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS302PX v.3	20240123	Product data sheet	-	PBSS302PX v.2
Modifications:	Nexperia. • Legal texts ha	this data sheet has been rede ve been adapted to the new o ing information" removed.		
PBSS302PX v.2	20091120	Product data sheet	-	PBSS302PX v.1
PBSS302PX v.1	20060823	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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